Package • Code

SSMini3-F3 • Pin Name 1: Base

> 2: Emitter 3: Collector

Marking Symbol: CK

Internal Connection

R

۰C

Σ

UNR91A4G

Silicon PNP epitaxial planar type

For digital circuits

Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

Absolute Maximum Ratings $T_a = 25^{\circ}C$ Parameter Symbol Rating Unit -50 V Collector-base voltage (Emitter open) V_{CBO} V Collector-emitter voltage (Base open) V_{CEO} -50Collector current Total power dissipation Junction temperature Storage temperature

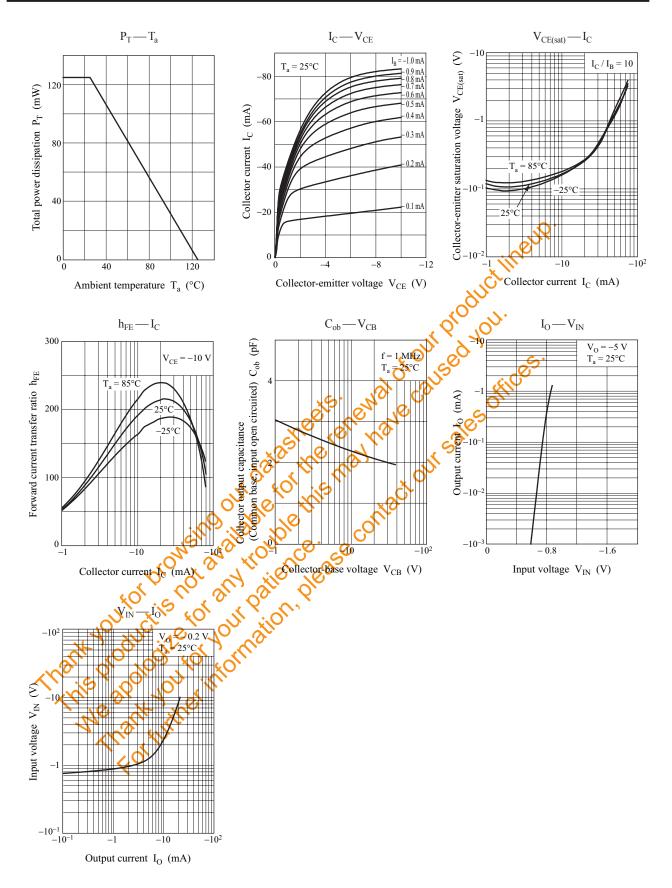
| ONST AVAILTOUT CE. SEC |
|---|
| Electrical Characteristics $T_a = 25^{\circ}C \pm 36$ |
| Deremeter C. Cumbol Condi |

| Parameter | Symbo | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|------|--------|------|
| Collector-base voltage (Emitter open) | Усво | $V_{\rm C} = -10 \mu {\rm A}, {\rm I}_{\rm E} = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | VCEO | $I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | Q _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | | | - 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{\rm CE} = -50$ V, $I_{\rm B} = 0$ | | | - 0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I _{EBO} | $V_{\rm EB} = -6$ V, $I_{\rm C} = 0$ | | | - 0.2 | mA |
| Forward current transfer ratio | h _{FE} | $V_{\rm CE} = -10$ V, $I_{\rm C} = -5$ mA | 80 | | | |
| Collector-emitter saturation Voltage | V _{CE(sat)} | $I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$ | | | - 0.25 | V |
| Output voltage high-level | V _{OH} | $V_{\rm CC}$ = -5 V, $V_{\rm B}$ = -0.5 V, $R_{\rm L}$ = 1 k Ω | -4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | - 0.2 | V |
| Input resistance | R ₁ | | -30% | 10 | +30% | kΩ |
| Resistance ratio | R_1/R_2 | | 0.17 | 0.21 | 0.25 | |
| Transition frequency | f _T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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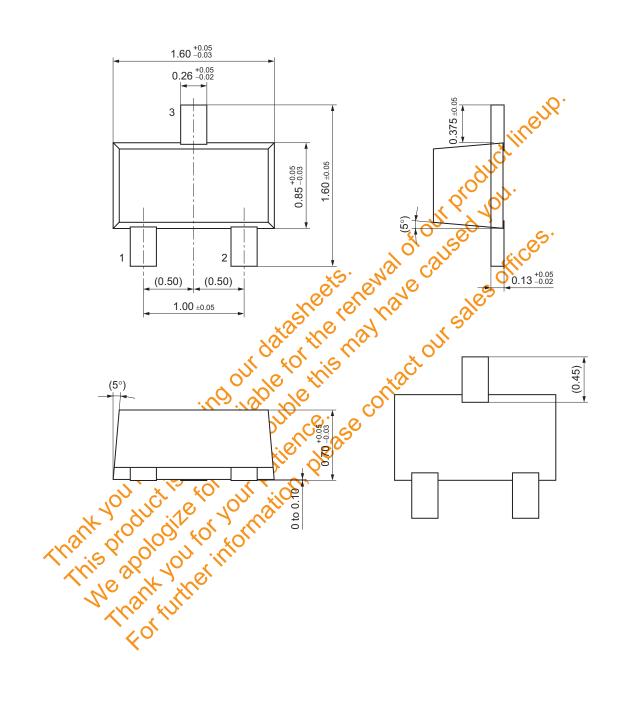
Panasonic



Panasonic

SSMini3-F3

Unit: mm



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